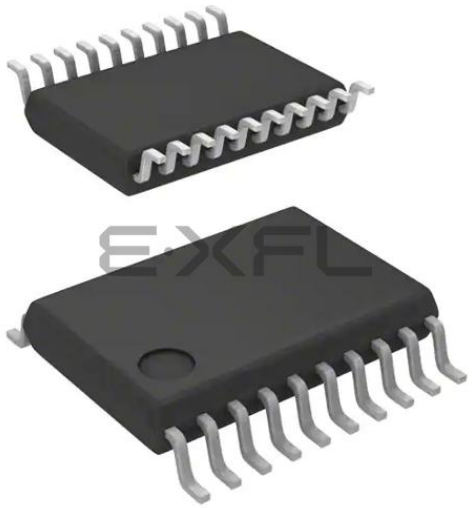
Renesas Electronics America Inc - R5F212H1SNSP#U0 Datasheet



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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	R8C
Core Size	16-Bit
Speed	8MHz
Connectivity	LINbus, SIO, UART/USART
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	15
Program Memory Size	4KB (4K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	256 x 8
Voltage - Supply (Vcc/Vdd)	2.2V ~ 5.5V
Data Converters	-
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	20-LSSOP (0.173", 4.40mm Width)
Supplier Device Package	20-LSSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f212h1snsp-u0

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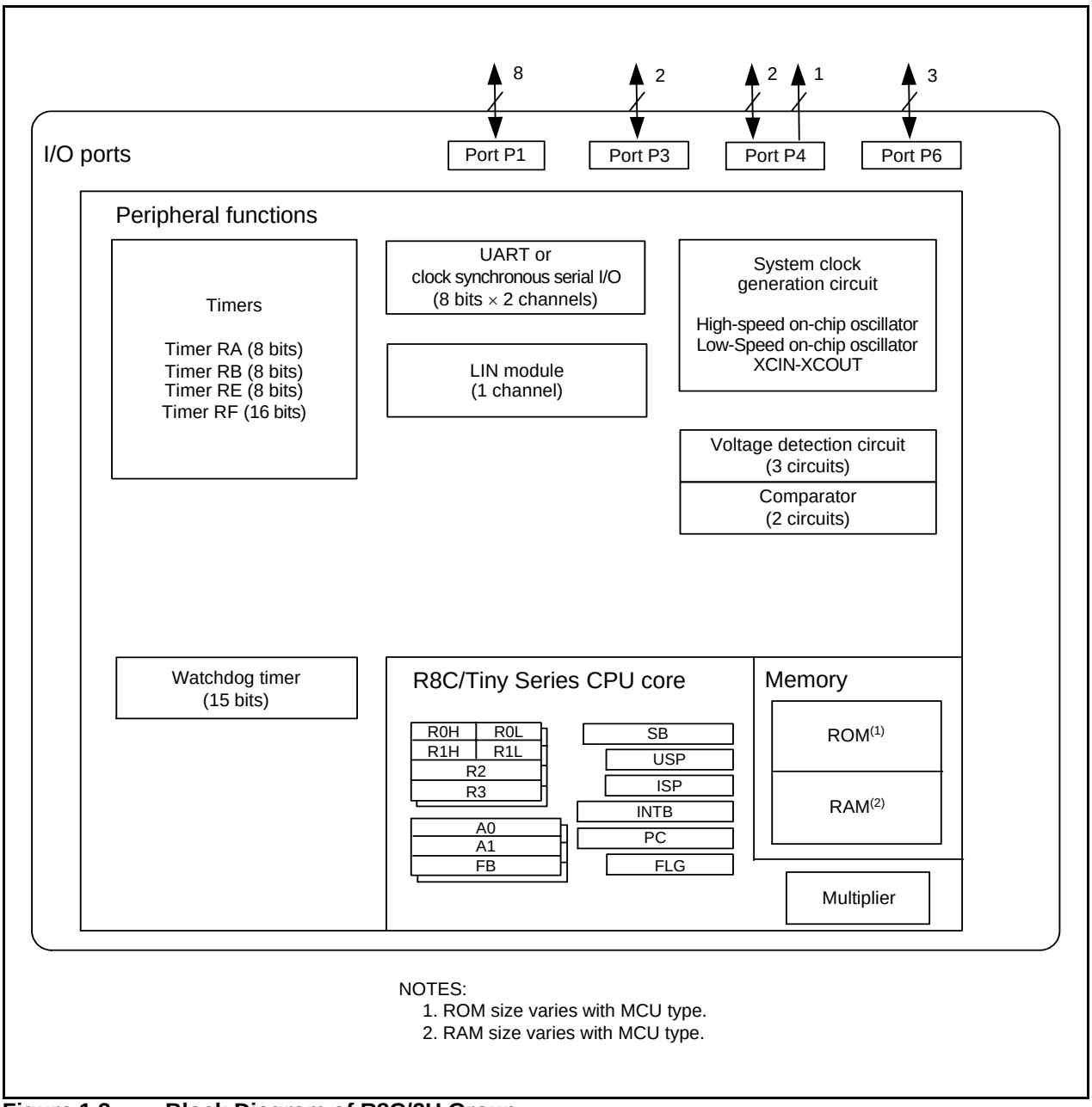
Table 1.1 Specifications for R8C/2H Group

Item	Function	Specification
CPU	Central processing unit	R8C/Tiny series core • Number of fundamental instructions: 89 • Minimum instruction execution time: 125 ns (System clock = 8 MHz, VCC = 2.7 to 5.5 V) 250 ns (System clock = 4 MHz, VCC = 2.2 to 5.5 V) • Multiplier: 16 bits × 16 bits → 32 bits • Multiply-accumulate instruction: 16 bits × 16 bits + 32 bits → 32 bits • Operation mode: Single-chip mode (address space: 1 Mbyte)
Memory	ROM, RAM	Refer to **Table 1.3 Product List for R8C/2H Group**.
Power Supply Voltage Detection	Voltage detection circuit	• Power-on reset • Voltage detection 3
Comparator		• 2 circuits (shared with voltage monitor 1 and voltage monitor 2) • External reference voltage input is available
I/O Ports		• Output-only: 1 • CMOS I/O ports: 15, selectable pull-up resistor
Clock	Clock generation circuits	• 2 circuits: On-chip oscillator (high-speed, low-speed) (high-speed on-chip oscillator has a frequency adjustment function), XCIN clock oscillation circuit (32 kHz) • Frequency divider circuit: Dividing selectable 1, 2, 4, 8, and 16 • Low power consumption modes: Standard operating mode (low-speed clock, high-speed on-chip oscillator, low-speed on-chip oscillator), wait mode, stop mode
		Real-time clock (timer RE)
Interrupts		• External: 3 sources, Internal: 17 sources, Software: 4 sources • Priority levels: 7 levels
Watchdog Timer		15 bits × 1 (with prescaler), reset start selectable
Timer	Timer RA	8 bits × 1 (with 8-bit prescaler) Timer mode (period timer), pulse output mode (output level inverted every period), event counter mode, pulse width measurement mode, pulse period measurement mode
	Timer RB	8 bits × 1 (with 8-bit prescaler) Timer mode (period timer), programmable waveform generation mode (PWM output), programmable one-shot generation mode, programmable wait one-shot generation mode
	Timer RE	8 bits × 1 Real-time clock mode (count seconds, minutes, hours, days of week), output compare mode
	Timer RF	16 bits × 1 (with capture/compare register pin and compare register pin) Input capture mode, output compare mode
Serial Interface	UART0, UART2	Clock synchronous serial I/O/UART × 2
LIN Module		Hardware LIN: 1 (timer RA, UART0)
Flash Memory		• Programming and erasure voltage: VCC = 2.7 to 5.5 V • Programming and erasure endurance: 100 times • Program security: ROM code protect, ID code check • Debug functions: On-chip debug, on-board flash rewrite function
Operating Frequency/Supply Voltage		System clock = 8 MHz (VCC = 2.7 to 5.5 V) System clock = 4 MHz (VCC = 2.2 to 5.5 V)
Current consumption		5 mA (VCC = 5 V, system clock = 8 MHz) 23 μA (VCC = 3 V, wait mode (low-speed on-chip oscillator on)) 0.7 μA (VCC = 3 V, stop mode, BGR trimming circuit disabled)
Operating Ambient Temperature		-20 to 85°C (N version) -40 to 85°C (D version)(1)
Package		20-pin LSSOP Package code: PLSP0020JB-A (previous code: 20P2F-A)

NOTE:
1. Specify the D version if D version functions are to be used.

1.3 Block Diagram

Figure 1.3 shows a Block Diagram of R8C/2H Group and Figure 1.4 shows a Block Diagram of R8C/2J Group.

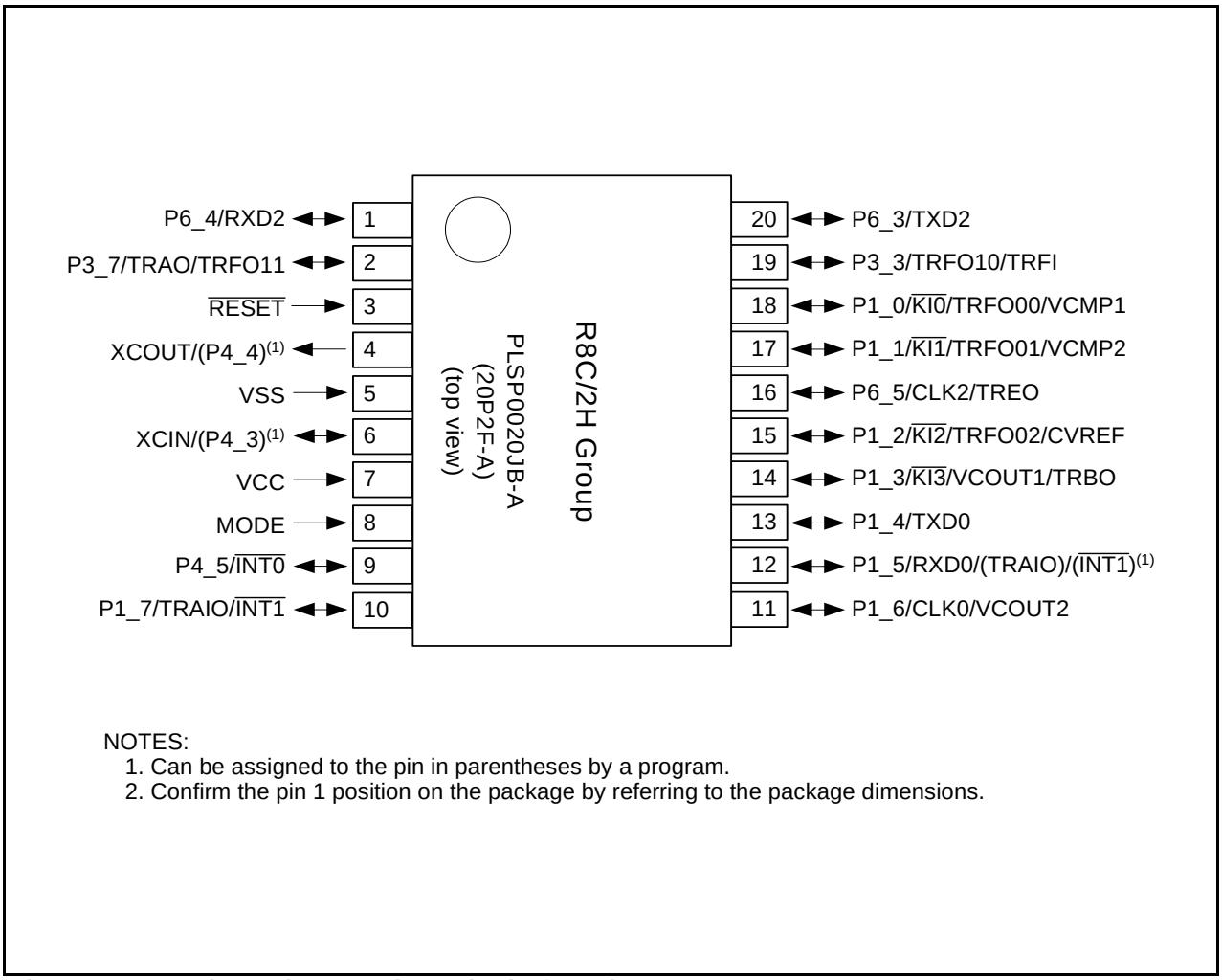


NOTES:
1. ROM size varies with MCU type.
2. RAM size varies with MCU type.

Figure 1.3 Block Diagram of R8C/2H Group

1.4 Pin Assignment

Figure 1.5 shows Pin Assignment (Top View) of R8C/2H Group. Table 1.5 outlines the Pin Name Information by Pin Number of R8C/2H Group.
Figure 1.6 shows Pin Assignment (Top View) of R8C/2J Group. Table 1.6 outlines the Pin Name Information by Pin Number of R8C/2J Group.



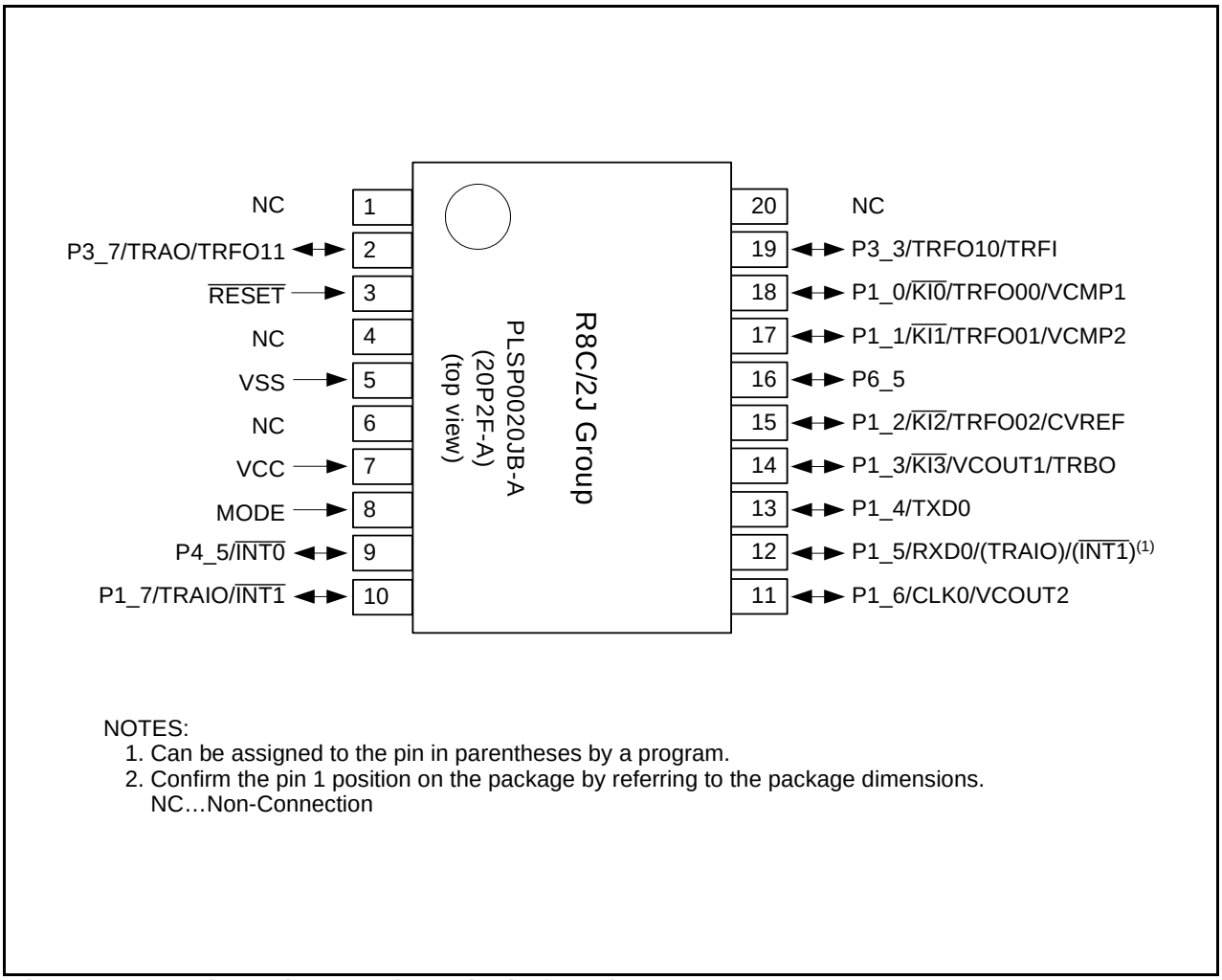
NOTES:
1. Can be assigned to the pin in parentheses by a program.
2. Confirm the pin 1 position on the package by referring to the package dimensions.

Figure 1.5 Pin Assignment (Top View) of R8C/2H Group

Table 1.5 Pin Name Information by Pin Number of R8C/2H Group

Pin Number	Control Pin	Port	I/O Pin Functions for of Peripheral Modules			
			Interrupt	Timer	Serial Interface	Comparator
1		P6_4			RXD2	
2		P3_7		TRAO/TRFO11		
3	$\overline{\text{RESET}}$					
4	XCOUT	(P4_4)				
5	VSS					
6	XCIN	(P4_3)				
7	VCC					
8	MODE					
9		P4_5	$\overline{\text{INT0}}$			
10		P1_7	$\overline{\text{INT1}}$	TRAIO		
11		P1_6			CLK0	VCOUT2
12		P1_5	($\overline{\text{INT1}}$)(1)	(TRAIO)(1)	RXD0	
13		P1_4			TXD0	
14		P1_3	$\overline{\text{KI3}}$	TRBO		VCOUT1
15		P1_2	$\overline{\text{KI2}}$	TRFO02		CVREF
16		P6_5		TREO	CLK2	
17		P1_1	$\overline{\text{KI1}}$	TRFO01		VCMP2
18		P1_0	$\overline{\text{KI0}}$	TRFO00		VCMP1
19		P3_3		TRFO10/TRFI		
20		P6_3			TXD2	

NOTE:
1. Can be assigned to the pin in parentheses by a program.



NOTES:
1. Can be assigned to the pin in parentheses by a program.
2. Confirm the pin 1 position on the package by referring to the package dimensions.
NC…Non-Connection

Figure 1.6 Pin Assignment (Top View) of R8C/2J Group

1.5 Pin Functions

Table 1.7 lists Pin Functions of R8C/2H Group and Table 1.8 lists Pin Functions of R8C/2J Group.

Table 1.7 Pin Functions of R8C/2H Group

Type	Symbol	I/O Type	Description
Power supply input	VCC, VSS	–	Apply 2.2 V to 5.5 V to the VCC pin. Apply 0 V to the VSS pin.
Reset input	$\overline{\text{RESET}}$	I	Input “L” on this pin resets the MCU.
MODE	MODE	I	Connect this pin to VCC via a resistor.
XCIN clock input	XCIN	I	These pins are provided for XCIN clock generation circuit I/O. Connect a crystal oscillator between the XCIN and XCOUT pins.(1) To use an external clock, input it to the XCIN pin and leave the XCOUT pin open.
XCIN clock output	XCOUT	O	
$\overline{\text{INT}}$ interrupt input	$\overline{\text{INT0}}$, $\overline{\text{INT1}}$	I	$\overline{\text{INT}}$ interrupt input pins
Key input interrupt	$\overline{\text{KI0}}$ to $\overline{\text{KI3}}$	I	Key input interrupt input pins
Timer RA	TRAIO	I/O	Timer RA I/O pin
	TRAO	O	Timer RA output pin
Timer RB	TRBO	O	Timer RB output pin
Timer RE	TREO	O	Divided clock output pin
Timer RF	TRFI	I	Timer RF input pin
	TRFO00 to TRFO02, TRFO10 to TRFO11	O	Timer RF output pins
Serial interface	CLK0, CLK2	I/O	Clock I/O pin
	RXD0, RXD2	I	Serial data input pin
	TXD0, TXD2	O	Serial data output pin
Comparator	VCMP1, VCMP2	I	Analog input pins to comparator
	CVREF	I	Reference voltage input pin to comparator
	VCOUT1, VCOUT2	O	Comparator output pins
I/O port	P1_0 to P1_7, P3_3, P3_7, P4_3, P4_5, P6_3 to P6_5	I/O	CMOS I/O ports. Each port has an I/O select direction register, allowing each pin in the port to be directed for input or output individually. Any port set to input can be set to use a pull-up resistor or not by a program.
Output port	P4_4	O	Output-only port

I: Input O: Output I/O: Input and output

NOTE:

1. Refer to the oscillator manufacturer for oscillation characteristics.

2.1 Data Registers (R0, R1, R2, and R3)

R0 is a 16-bit register for transfer, arithmetic, and logic operations. The same applies to R1 to R3. R0 can be split into high-order bits (R0H) and low-order bits (R0L) to be used separately as 8-bit data registers. R1H and R1L are analogous to R0H and R0L. R2 can be combined with R0 and used as a 32-bit data register (R2R0). R3R1 is analogous to R2R0.

2.2 Address Registers (A0 and A1)

A0 is a 16-bit register for address register indirect addressing and address register relative addressing. It is also used for transfer, arithmetic, and logic operations. A1 is analogous to A0. A1 can be combined with A0 to be used as a 32-bit address register (A1A0).

2.3 Frame Base Register (FB)

FB is a 16-bit register for FB relative addressing.

2.4 Interrupt Table Register (INTB)

INTB is a 20-bit register that indicates the start address of an interrupt vector table.

2.5 Program Counter (PC)

PC is 20 bits wide and indicates the address of the next instruction to be executed.

2.6 User Stack Pointer (USP) and Interrupt Stack Pointer (ISP)

The stack pointers (SP), USP, and ISP, are each 16 bits wide. The U flag of FLG is used to switch between USP and ISP.

2.7 Static Base Register (SB)

SB is a 16-bit register for SB relative addressing.

2.8 Flag Register (FLG)

FLG is an 11-bit register indicating the CPU state.

2.8.1 Carry Flag (C)

The C flag retains carry, borrow, or shift-out bits that have been generated by the arithmetic and logic unit.

2.8.2 Debug Flag (D)

The D flag is for debugging only. Set it to 0.

2.8.3 Zero Flag (Z)

The Z flag is set to 1 when an arithmetic operation results in 0; otherwise to 0.

2.8.4 Sign Flag (S)

The S flag is set to 1 when an arithmetic operation results in a negative value; otherwise to 0.

2.8.5 Register Bank Select Flag (B)

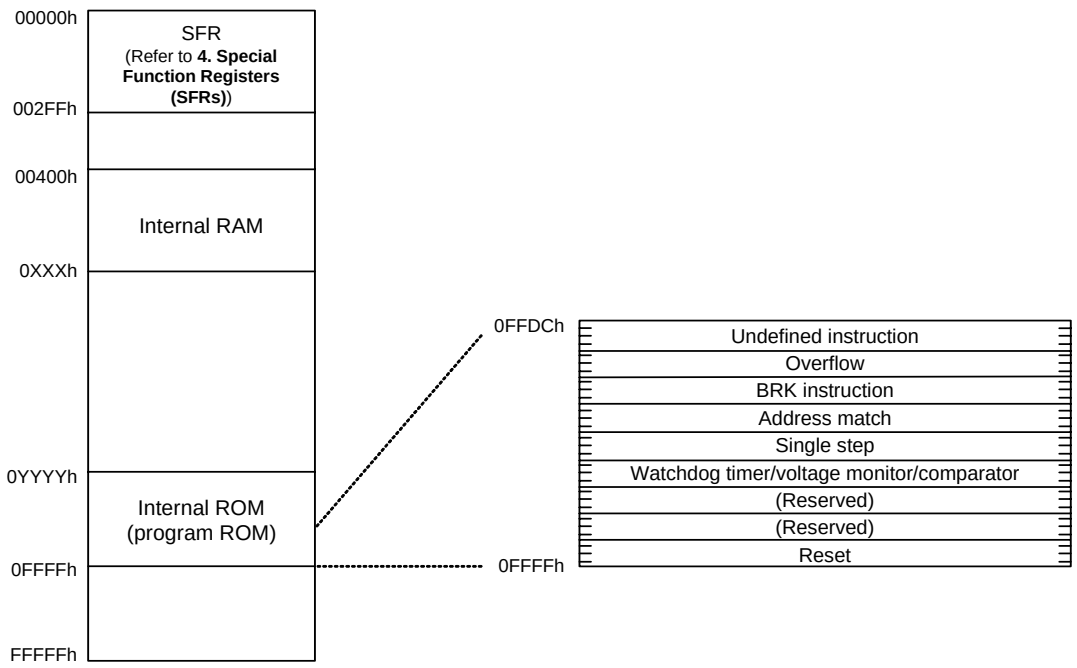
Register bank 0 is selected when the B flag is 0. Register bank 1 is selected when this flag is set to 1.

2.8.6 Overflow Flag (O)

The O flag is set to 1 when an operation results in an overflow; otherwise to 0.

3. Memory

Figure 3.1 is a Memory Map of R8C/2H Group and Figure 3.2 is a Memory Map of R8C/2J Group. The R8C/2H group has 1 Mbyte of address space from addresses 00000h to FFFFFh.
The internal ROM is allocated lower addresses, beginning with address 0FFFFh. For example, a 4-Kbyte internal ROM area is allocated addresses 0F000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.
The internal RAM is allocated higher addresses beginning with address 00400h. For example, a 256-bytes internal RAM area is allocated addresses 00400h to 004FFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.



NOTE:
1. The blank regions are reserved. Do not access locations in these regions.

Part Number	Internal ROM		Internal RAM	
	Size	Address 0YYYYh	Size	Address 0XXXXh
R5F212H1SNSP, R5F212H1SDSP	4 Kbytes	0F000h	256 bytes	004FFh
R5F212H2SNSP, R5F212H2SDSP	8 Kbytes	0E000h	384 bytes	0057Fh

Figure 3.1 Memory Map of R8C/2H Group

4. Special Function Registers (SFRs)

An SFR (special function register) is a control register for a peripheral function. Tables 4.1 to 4.12 list the special function registers.

Table 4.1 SFR Information (1)[1]

Address	Register	Symbol	After reset
0000h			
0001h			
0002h			
0003h			
0004h	Processor Mode Register 0	PM0	00h
0005h	Processor Mode Register 1	PM1	00h
0006h	System Clock Control Register 0	CM0	01011000b
0007h	System Clock Control Register 1	CM1	00h
0008h			
0009h			
000Ah	Protect Register	PRCR	00h
000Bh			
000Ch	System Clock Select Register[3]	OCD	00000100b
000Dh	Watchdog Timer Reset Register	WDTR	XXh
000Eh	Watchdog Timer Start Register	WDTS	XXh
000Fh	Watchdog Timer Control Register	WDC	00X11111b
0010h	Address Match Interrupt Register 0	RMAD0	00h
0011h			00h
0012h			00h
0013h	Address Match Interrupt Enable Register	AIER	00h
0014h	Address Match Interrupt Register 1	RMAD1	00h
0015h			00h
0016h			00h
0017h			
0018h			
0019h			
001Ah			
001Bh			
001Ch	Count Source Protection Mode Register	CSPR	00h 10000000b[2]
001Dh			
001Eh			
001Fh			
0020h	High-Speed On-Chip Oscillator Control Register 0	HRA0	00h
0021h	High-Speed On-Chip Oscillator Control Register 1	HRA1	When Shipping
0022h	High-Speed On-Chip Oscillator Control Register 2	HRA2	00h
0023h			
0024h			
0025h			
0026h			
0027h			
0028h	Clock Prescaler Reset Flag[3]	CPSRF	00h
0029h	High-Speed On-Chip Oscillator Control Register 4	FRA4	When Shipping
002Ah			
002Bh	High-Speed On-Chip Oscillator Control Register 6	FRA6	When Shipping
002Ch			
002Dh			
002Eh	BGR Trimming Auxiliary Register A	BGRTRMA	When Shipping
002Fh	BGR Trimming Auxiliary Register B	BGRTRMB	When Shipping

X: Undefined
NOTES:
1. The blank regions are reserved. Do not access locations in these regions.
2. The CSPROINI bit in the OFS register is set to 0.
3. This register is not implemented in the R8C/2J Group.

Table 4.12 SFR Information (12)(1)

Address	Register	Symbol	After reset
02B0h			
02B1h			
02B2h			
02B3h			
02B4h			
02B5h			
02B6h			
02B7h			
02B8h			
02B9h			
02BAh			
02BBh			
02BCh			
02BDh			
02BEh			
02BFh			
02C0h			
02C1h			
02C2h			
02C3h			
02C4h			
02C5h			
02C6h			
02C7h			
02C8h			
02C9h			
02CAh			
02CBh			
02CCh			
02CDh			
02CEh			
02CFh			
02D0h			
02D1h			
02D2h			
02D3h			
02D4h			
02D5h			
02D6h			
02D7h			
02D8h			
02D9h			
02DAh			
02DBh			
02DCh			
02DDh			
02DEh			
02DFh			
02E0h			
02EFh			
02F0h			
02F1h			
02F2h			
02F3h			
02F4h			
02F5h			
02F6h			
02F7h			
02F8h			
02F9h			
02FAh			
02FBh	Pin Select Register 4	PINSR4	00h
02FCh			
02FDh			
02FEh			
02FFh	Timer RF Output Control Register	TRFOUT	00h
FFFFh	Option Function Select Register	OFS	(Note 2)

X: Undefined
NOTES:
1. The blank regions are reserved. Do not access locations in these regions.
2. The OFS register cannot be changed by a program. Use a flash programmer to write to it.

Table 5.3 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)		100(3)	–	–	times
–	Byte program time		–	50	400	µs
–	Block erase time		–	0.4	9	s
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.2	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time(7)	Ambient temperature = 55°C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = 0 to 60°C, unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 100 or 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erase count of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.4 Voltage Detection 0 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det0}	Voltage detection level		2.2	2.3	2.4	V
–	Voltage detection circuit self power consumption	VCA25 = 1, V_{CC} = 5.0 V	–	0.9	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(2)		–	–	300	µs
Vccmin	MCU operating voltage minimum value		2.2	–	–	V

NOTES:
1. The measurement condition is V_{CC} = 2.2 to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version).
2. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA25 bit in the VCA2 register to 0.

Table 5.5 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det1}	Voltage detection level(4)		2.70	2.85	3.00	V
–	Voltage monitor 1 interrupt request generation time(2)		–	40	–	µs
–	Voltage detection circuit self power consumption	VCA26 = 1, V_{CC} = 5.0 V	–	0.6	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(3)		–	–	100	µs

NOTES:
1. The measurement condition is V_{CC} = 2.2 to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version).
2. Time until the voltage monitor 1 interrupt request is generated after the voltage passes V_{det1}.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.
4. This parameter shows the voltage detection level when the power supply drops.
   The voltage detection level when the power supply rises is higher than the voltage detection level when the power supply drops by approximately 0.1 V.

Table 5.6 Voltage Detection 2 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det2}	Voltage detection level		3.3	3.6	3.9	V
–	Voltage monitor 2 interrupt request generation time(2)		–	40	–	µs
–	Voltage detection circuit self power consumption	VCA27 = 1, V_{CC} = 5.0 V	–	0.6	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(3)		–	–	100	µs

NOTES:
1. The measurement condition is V_{CC} = 2.2 to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version).
2. Time until the voltage monitor 2 interrupt request is generated after the voltage passes V_{det2}.
3. Necessary time until the voltage detection circuit operates after setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.

Table 5.13 Electrical Characteristics (2) [Vcc = 5 V]
(Topr = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
ICC	Power supply current (VCC = 3.3 to 5.5 V) Single-chip mode, output pins are open, other pins are VSS	High-speed on-chip oscillator mode	High-speed on-chip oscillator on = 8 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	5	8	mA
			High-speed on-chip oscillator on = 8 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2	–	mA
		Low-speed on-chip oscillator mode	High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR47 = 1	–	130	300	µA
		Low-speed clock mode	High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (low drive) FMR47 = 1	–	130	300	µA
			High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (low drive) Program operation on RAM Flash memory off, FMSTP = 1	–	30	–	µA
		Wait mode	High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	25	75	µA
			High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	23	60	µA
			High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (high drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1 BGR trimming circuit disabled (BGRCR0 = 1)	–	4	–	µA
			High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (low drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1 BGR trimming circuit disabled (BGRCR0 = 1)	–	2.2	–	µA
			High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (high drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1 BGR trimming circuit enabled (BGRCR0 = 0)	–	8	–	µA
			High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (low drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1 BGR trimming circuit enabled (BGRCR0 = 0)	–	6	–	µA
		Stop mode	XCIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0 BGR trimming circuit disabled (BGRCR0 = 1)	–	0.8	3	µA
			XCIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0 BGR trimming circuit disabled (BGRCR0 = 1)	–	1.2	–	µA
			XCIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0 BGR trimming circuit enabled (BGRCR0 = 0)	–	5	8	µA
			XCIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0 BGR trimming circuit enabled (BGRCR0 = 0)	–	5.5	–	µA

Timing Requirements
(Unless Otherwise Specified: V_{CC} = 5 V, V_{SS} = 0 V at T_{opr} = 25°C) [V_{CC} = 5 V]

Table 5.14 XCIN Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XCIN)}$	XCIN input cycle time	14	–	µs
$t_{WH(XCIN)}$	XCIN input “H” width	7	–	µs
$t_{WL(XCIN)}$	XCIN input “L” width	7	–	µs

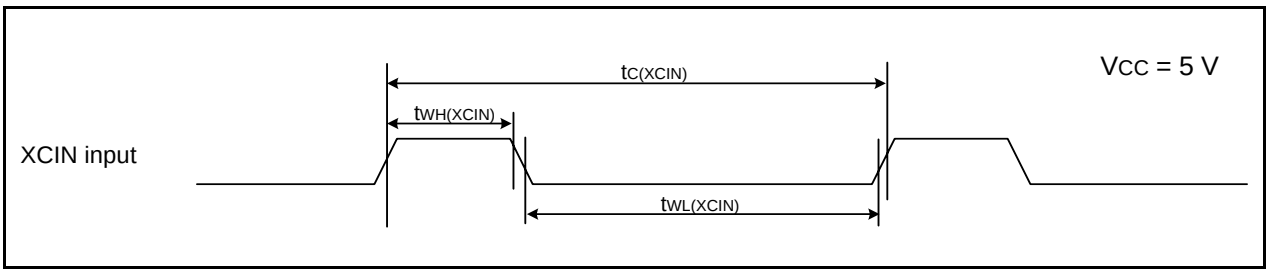


Figure 5.3 XCIN Input Timing Diagram when V_{CC} = 5 V

Table 5.15 TRAIO Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	100	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	40	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	40	–	ns

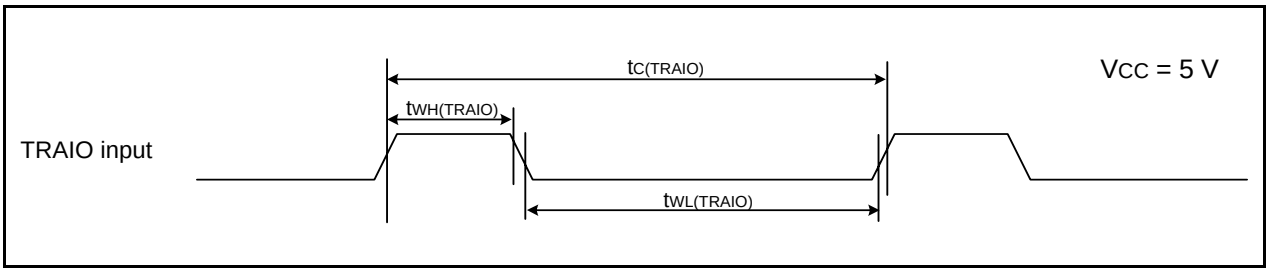


Figure 5.4 TRAIO Input Timing Diagram when V_{CC} = 5 V

Table 5.16 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	200	–	ns
$t_{W(CKH)}$	CLKi input “H” width	100	–	ns
$t_{W(CKL)}$	CLKi input “L” width	100	–	ns
$t_{d(C-Q)}$	TXDi output delay time	–	50	ns
$t_{h(C-Q)}$	TXDi hold time	0	–	ns
$t_{su(D-C)}$	RXDi input setup time	50	–	ns
$t_{h(C-D)}$	RXDi input hold time	90	–	ns

i = 0 or 2

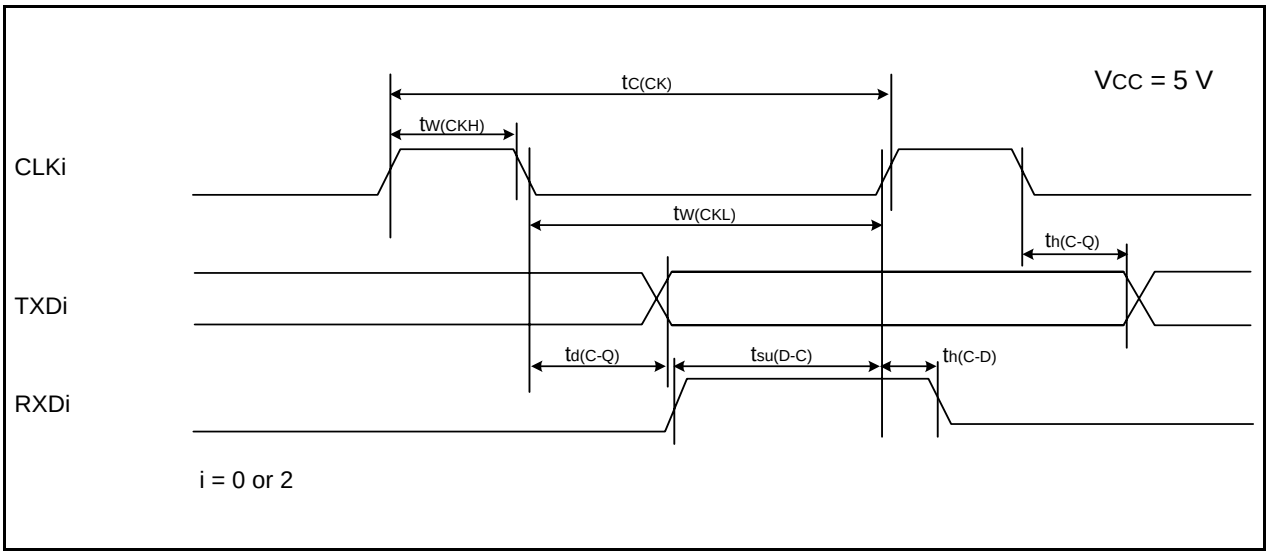


Figure 5.5 Serial Interface Timing Diagram when VCC = 5 V

Table 5.17 External Interrupt $\overline{INTi}$ (i = 0 or 1) Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INTi}$ input “H” width	250(1)	–	ns
$t_{W(INL)}$	$\overline{INTi}$ input “L” width	250(2)	–	ns

NOTES:
1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

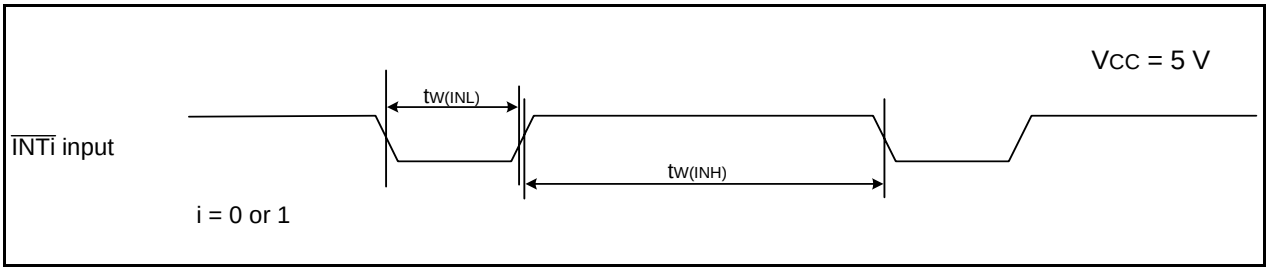


Figure 5.6 External Interrupt $\overline{INTi}$ Input Timing Diagram when VCC = 5 V

Table 5.18 Electrical Characteristics (3) [V_{CC} = 3 V]

Symbol	Parameter		Condition	Standard			Unit
				Min.	Typ.	Max.	
V_{OH}	Output “H” voltage		I_{OH} = –1 mA	V_{CC} – 0.5	–	V_{CC}	V
V_{OL}	Output “L” voltage		I_{OL} = 1 mA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, RXD0, RXD2, CLK0, CLK2		0.1	0.3	–	V
		$\overline{RESET}$		0.1	0.4	–	V
I_{IH}	Input “H” current		VI = 3 V, V_{CC} = 3 V	–	–	4.0	µA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 3 V	–	–	–4.0	µA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 3 V	66	160	500	kΩ
R_{fXCIN}	Feedback resistance	XCIN		–	18	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode	1.8	–	–	V

NOTE:
1. V_{CC} =2.7 to 3.3 V at T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.

Table 5.32 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)		100(3)	–	–	times
–	Byte program time		–	50	400	µs
–	Block erase time		–	0.4	9	s
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.2	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time(7)	Ambient temperature = 55°C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = 0 to 60°C, unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 100 or 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erase count of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

Timing requirements
(Unless Otherwise Specified: V_{CC} = 3 V, V_{SS} = 0 V at T_{opr} = 25°C) [V_{CC} = 3 V]

Table 5.48 TRAIO Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	300	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	120	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	120	–	ns

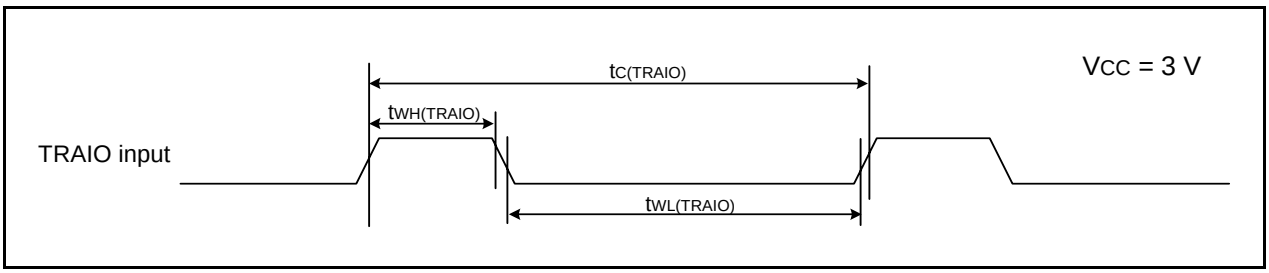


Figure 5.20 TRAIO Input Timing Diagram when V_{CC} = 3 V

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